

B1
Panel

48. (Amended) The method in claim 47, wherein exposing the wafer in situ to a reducing environment comprises exposing the wafer to silane gas and wherein said step of exposing said wafer in situ to an N₂/H₂ plasma comprises exposing said wafer in situ to said N₂/H₂ plasma prior to said step of exposing said wafer to silane gas.

Please add new claims 76-79 as follows:

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C1

--76. (New) A method of treating a wafer, comprising:
depositing a first conductive layer onto the wafer;
exposing the wafer in situ to a reducing environment; and
depositing a second conductive layer; and
exposing the wafer to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof.

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77. (New) The method of claim 76 wherein exposing the wafer in situ to a reducing environment comprises exposing the wafer to silane gas.

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C2

78. (New) The method of claim 76 wherein exposing the wafer to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof comprises exposing the wafer to this selection prior to exposing the wafer in situ to a reducing environment.

79. (New) The method of claim 76 wherein exposing the wafer to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof comprises exposing the wafer to this selection prior to depositing the second conductive layer.--